

Amendments to the Specification

Page 43, beginning with line 2, amend the abstract as follows.

A wet treatment method useful in ~~at least~~ one of a chemical processing ~~step~~ and a rinsing step performed upon fabrication of semiconductor devices ~~is disclosed. According to this method,~~ a A substrate ~~under treatment~~ is treated with a desired liquid while ~~causing revolving~~ the substrate ~~to revolve~~ around an axis of rotation outside the substrate itself ~~instead of allowing the substrate to rotate about the axis of rotation~~ such that the liquid flowing on a surface of the substrate is maintained flowing under a centrifugal force greater than gravitation. The substrate is treated while supplying a ~~fresh liquid of the same kind as the desired~~ liquid at a flow rate at least equal to a discharge rate of the ~~desired~~ liquid only in a direction conforming with that of the centrifugal force or with that of a flow of the liquid flowing on the surface of the substrate under the centrifugal force. The substrate surface is, ~~therefore,~~ evenly treated ~~at the surface thereof~~ with the ~~desired~~ liquid while avoiding ~~development of such a situation that~~ flows of the liquid ~~run~~ running against each other ~~on the surface of the substrate~~ or a flow of the liquid ~~stagnates~~ stagnating on the surface of the substrate. ~~A wet treatment apparatus suitable for use in practicing the wet treatment method is also disclosed.~~